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Application No. 10/007,754	Prepared by	25H .	Tracking Number	05974680
Examiner-GAU Flynn - 2820	Date	0723-04	Week Date	628-04
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INFORMATION DISCLOSURE				Filing Date	
STATEMENT BY APPLICANT (use as many sheets as necessary)		First Named Inventor	Darrell G. Hill		
		Group Art Unit			
		Examiner Name			
Sheet	2	of	2	Attorney Docket Number	SC10776P C01

		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-Issue number(s), publisher, city and/or country where published.				
	19	H. Lin et al., "Super-Gain AlGaAs/GaAs Heterojunction Bipolar Transistors Using An Emitter Edge-Thinning Design", American Institute of Physics, appl. Phys. Letter 47(8), 15 October 1985, pages 839-841.				
	20	W. Lee et al., "Effect of Emitter-Base Spacing on the current Gain of AlGaAs/GaAs Heterojunction Bipolar Transistors", IEEE Electronic Device Letters, Vol. 10, No. 5, May 1989, pages 200-202.	•			
	21	Wolf, S., "Silicon Processing for the VLSI Era, Volume 2", Process Integration, Sunset Beach, CA, 1990, pages 486-488.	-			
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